

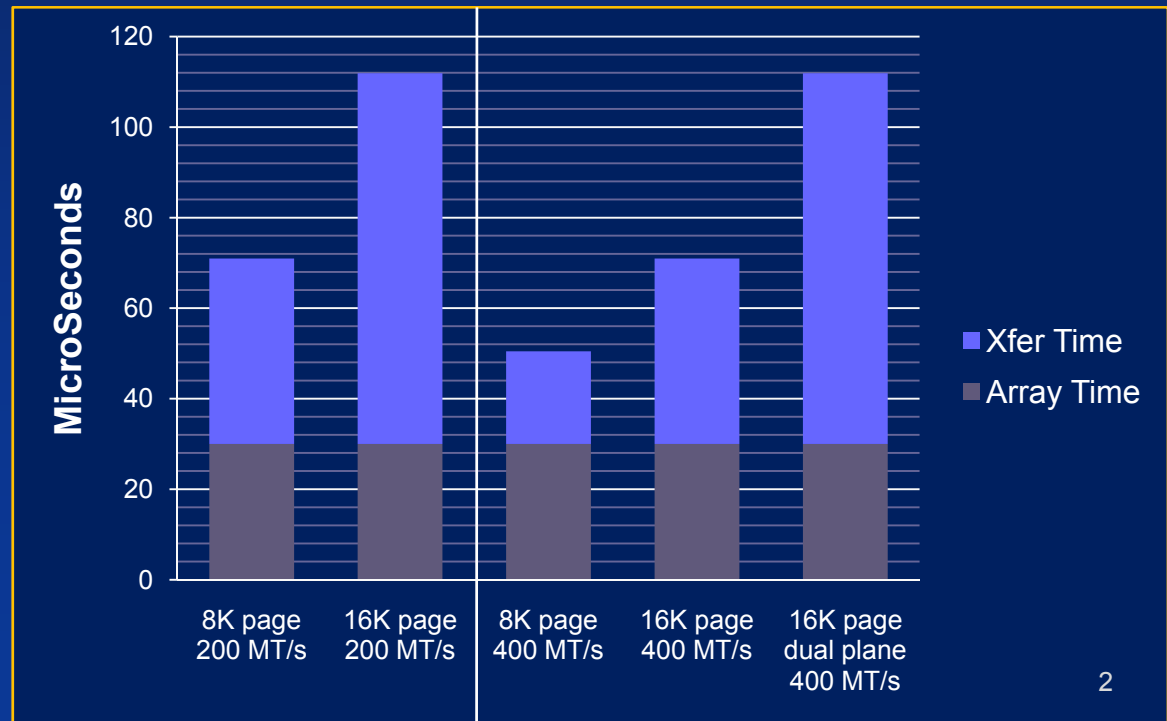


400 MT/s NAND Interface Solutions

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Why 400 MT/s Interface Speeds?

- NAND architectures are moving toward larger data transfer sizes
- Increased bandwidth
 - High-performance computing applications
 - High-density SSDs
 - USB 3.0
- Reduced latency





400 MT/s NAND Interface Solutions

- ONFI 3.0 NV-DDR2
 - Released March 2011
 - ONFI 3.0 Webinar: micron.com/ONFI-3
- Toggle Mode 2.0
 - Announced July 2010
- Work occurring in JEDEC on 400 MT/s
- Reduced CIO
 - Removes features to reduce loading



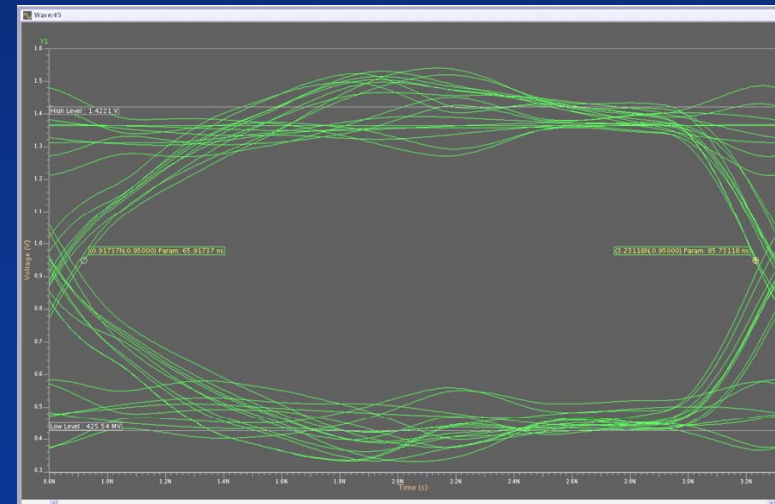
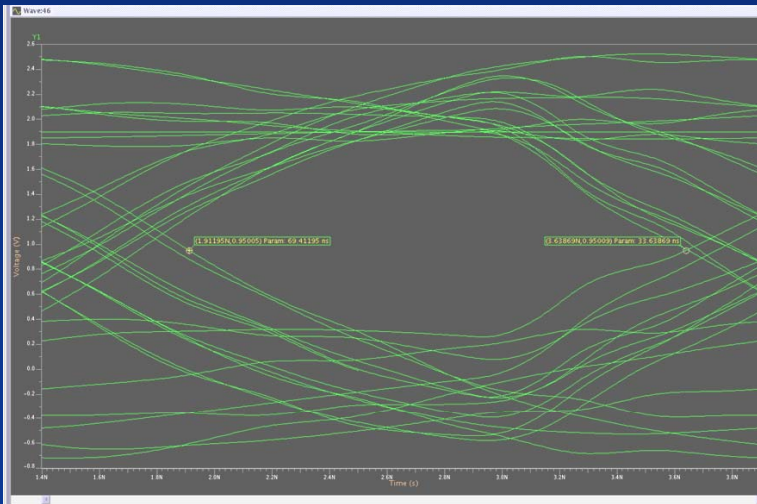
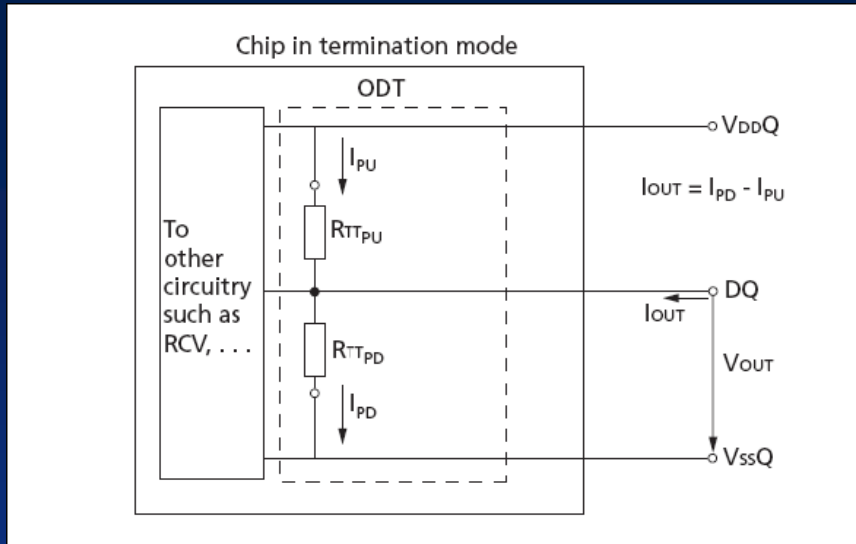
Toggle Mode 2.0

- 400 MT/s DDR interface
 - Compatible with ONFI 3.0 NV-DDR2
- Differential signaling (RE and DQS)
- On-die termination
- External V_{REFQ}
- Reduced signaling (SSTL_18)
- Warm-up cycles

ONFI 3.0 NV-DDR2

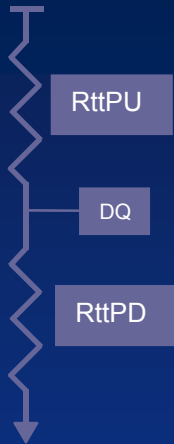
- 400 MT/s DDR interface
 - Superset of Toggle Mode 2.0
- Differential signaling (RE and DQS)
- On-die termination
- External V_{REFQ}
- Reduced signaling (SSTL_18)
- Warm-up cycles
- Matrix on-die termination
- Volume addressing

Benefits of Termination



Power Costs of Termination

To achieve R_{TT} of 50 ohms:



$$R_{TTPU} = 100 \text{ ohms}$$

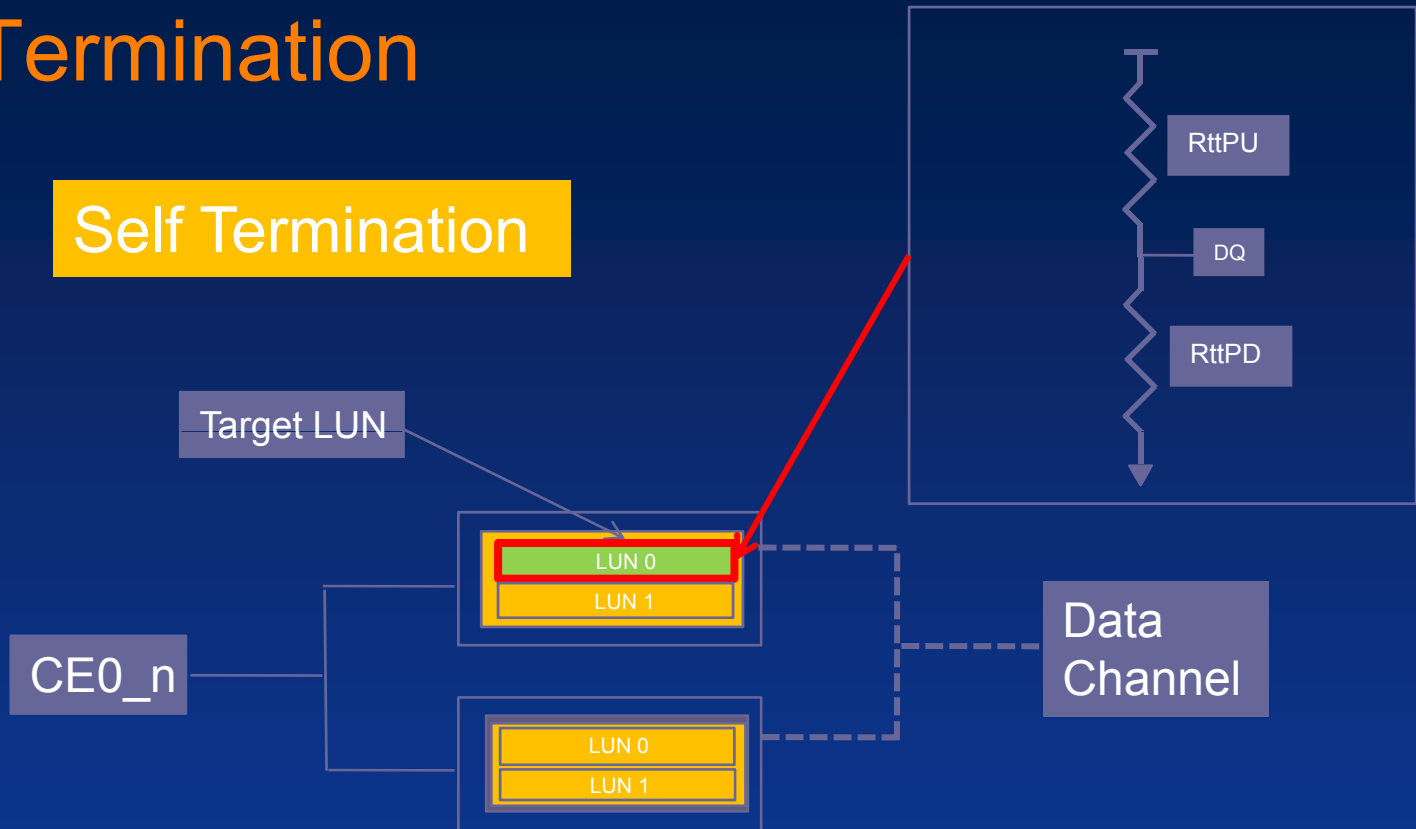
$$R_{TTPD} = 100 \text{ ohms}$$

With 1.8V V_{CCQ} , each DQ draws
~9mA

For all terminated signals, this amounts to ~160mW per channel to achieve 50 ohms termination with linear termination

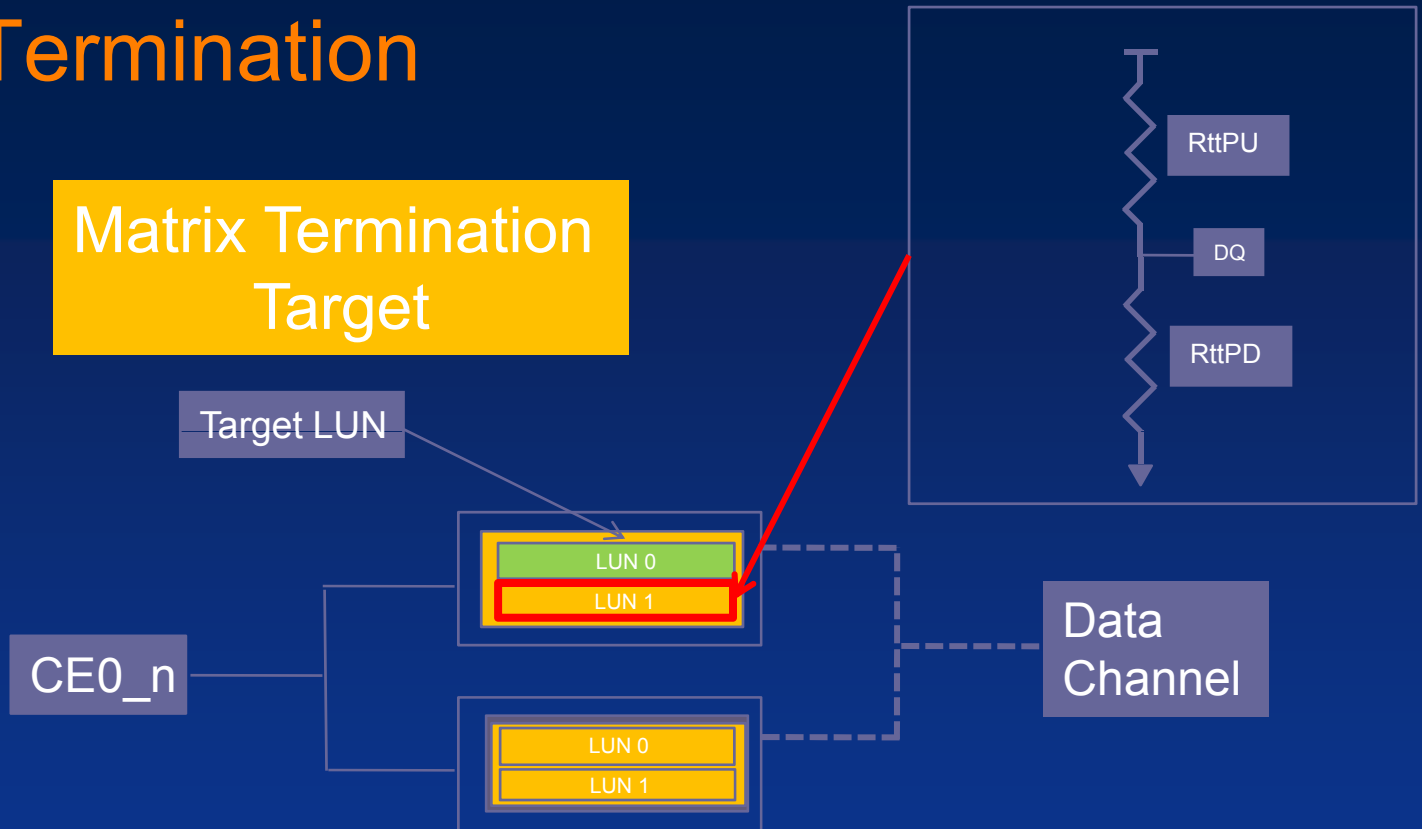
Matrix Termination vs. Self Termination

Self Termination



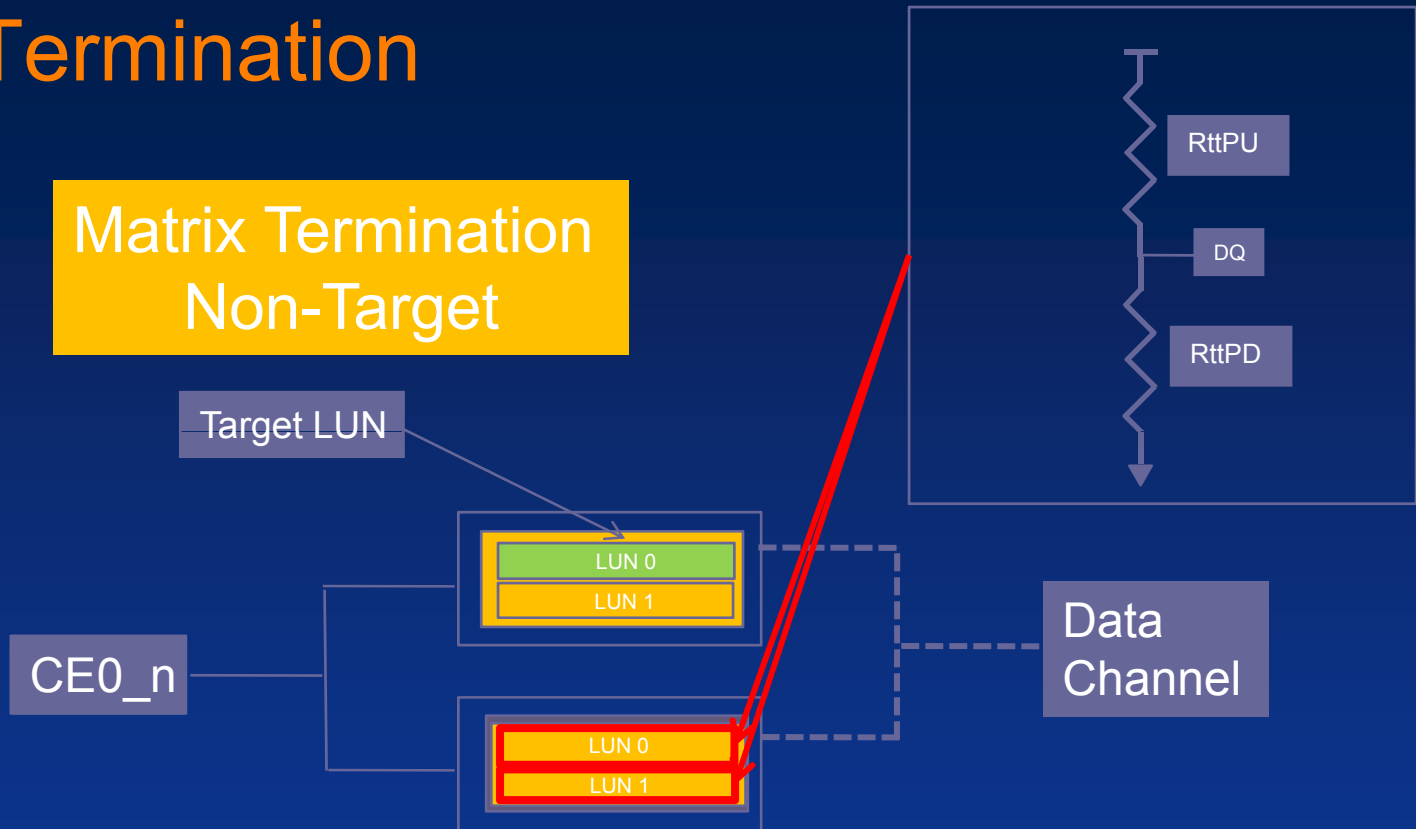
- Target only termination available
- If supported for reads, output drivers cannot be used for termination

Matrix Termination vs. Self Termination



- Target or non-target termination capable
- Supported for reads and writes

Matrix Termination vs. Self Termination

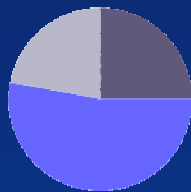


- Multiple LUNs can be terminators, providing a flexible array of termination values and locations

Timing Budget Considerations

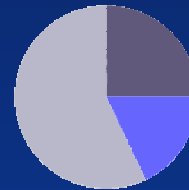
- With heavy loading and long trace lengths, slew rates can become very slow.

ONFI 3.0 400 MT/s timing budget
1V/nS input slew rate



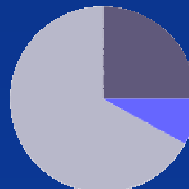
■ Controller
■ Channel
■ NAND

ONFI 3.0 400 MT/s timing budget
0.3V/nS input slew rate



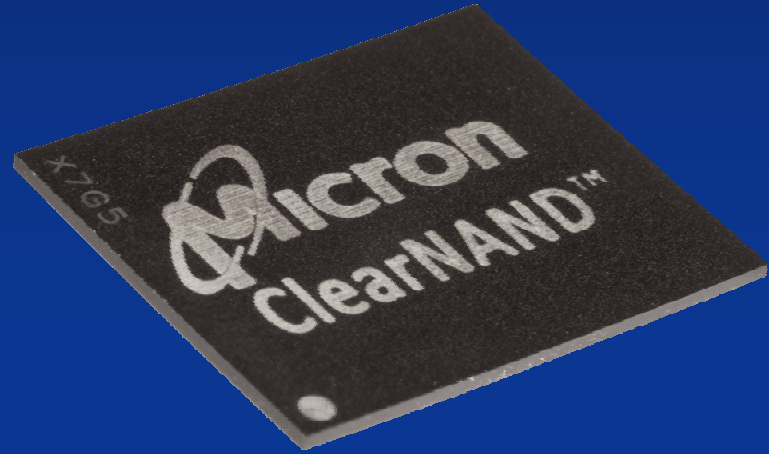
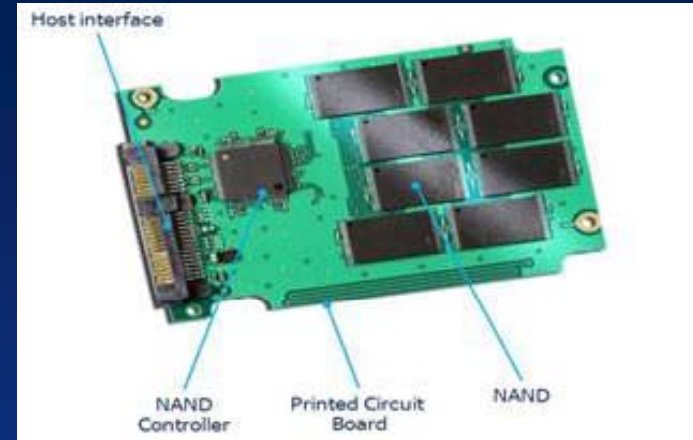
■ Controller
■ Channel
■ NAND

TM 2.0 400 MT/s timing budget
0.3V/nS input slew rate



■ Controller
■ Channel
■ NAND

Topology Considerations





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